

2N5060 THRU 2N5064

SILICON CONTROLLED RECTIFIER
0.8 AMP, 30 THRU 200 VOLTS



TO-92 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5060 series types are epoxy molded Silicon Controlled Rectifiers designed for control systems and sensing circuit applications.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N5060	2N5061	2N5062	2N5063	2N5064	UNITS
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	30	60	100	150	200	V
RMS On-State Current ($T_C=60^\circ\text{C}$)	$I_T(\text{RMS})$			0.8			A
Peak One Cycle Surge	I_{TSM}			10			A
Peak Forward Gate Current ($t_p=20\mu\text{s}$)	I_{GM}			1.0			A
Peak Reverse Gate Voltage	V_{GM}			5.0			V
Peak Gate Power Dissipation	P_{GM}			2.0			W
Average Gate Power Dissipation ($t=20\mu\text{s}$)	$P_G (AV)$			0.1			W
Storage Temperature	T_{stg}			-40 to +150			$^\circ\text{C}$
Junction Temperature	T_J			-40 to +125			$^\circ\text{C}$

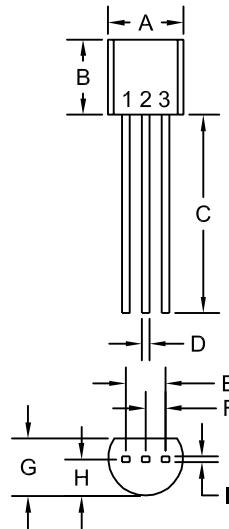
ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, R_{GK}=1K\Omega$			1.0	μA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}, R_{GK}=1K\Omega$			50	μA
I_{GT}	$V_D=7.0V, R_L=100\Omega, R_{GK}=1K\Omega$			200	μA
I_{GT}	$V_D=7.0V, R_L=100\Omega, R_{GK}=1K\Omega, T_C=-65^\circ\text{C}$			350	μA
I_H	$R_{GK}=1K\Omega$			5.0	mA
I_H	$R_{GK}=1K\Omega, T_C=-65^\circ\text{C}$			10	mA
V_{GT}	$V_D=7.0V, R_L=100\Omega$			0.8	V
V_{GT}	$V_D=7.0V, R_L=100\Omega, T_C=-65^\circ\text{C}$			1.2	V
V_{GT}	$V_D=7.0V, R_L=100\Omega, T_C=125^\circ\text{C}$	0.1			V
V_{TM}	$I_{TM}=1.2A$			1.7	V
dv/dt	$V_D=0.67V \times V_{DRM}, T_C=125^\circ\text{C}, R_{GK}=1K\Omega$		30		V/ μs
t_q	$V_D=0.67V \times V_{DRM}, T_C=125^\circ\text{C}, R_{GK}=1K\Omega$			200	μs

R4 (25-August 2004)

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TO-92 CASE - MECHANICAL OUTLINE



R1

LEAD CODE:

- 1) CATHODE
- 2) GATE
- 3) ANODE

MARKING CODE:

FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R4 (25-August 2004)

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.